



# PJM3407PSA

## P Enhancement Field Effect Transistor

### DESCRIPTION

The PJM3407PSA uses advanced trench technology to provide excellent  $R_{DS(on)}$  with low gate charge.

This device is suitable for use as a load switch in PWM applications.

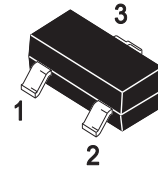
### FEATURES

$V_{DS(V)} = -30V$

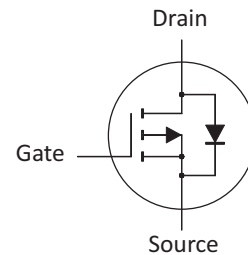
$I_D = -4.1A$

$R_{DS(on)} < 60m\Omega @ -10V$

$R_{DS(on)} < 87m\Omega @ -4.5V$



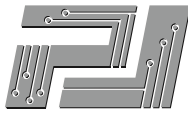
1Gate 2Source 3Drain  
SOT-23 Plastic Package



### ABSOLUTE MAXIMUM RATINGS

( $T_A=25^\circ C$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-4.1	A
Power Dissipation <sup>(1)</sup>	$P_D$	1.4	W
Thermal Resistance from Junction to Ambient <sup>(2)</sup> ( $t \leq 10s$ )	$R_{\theta JA}$	90	$^\circ C/W$
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{STG}$	-55~+150	$^\circ C$



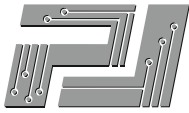
### ELECTRICAL CHARACTERISTICS

$T_A = 25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -24V, V_{GS} = 0V$			-1	$\mu A$
Gate-source leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
Drain-source on-resistance <sup>(3)</sup>	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -4.1A$		50	60	m $\Omega$
		$V_{GS} = -4.5V, I_D = -3A$		68	87	m $\Omega$
Forward transconductance <sup>(3)</sup>	$g_{FS}$	$V_{DS} = -5V, I_D = -4A$	5.5			S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.4	-3	V
Diode forward voltage <sup>(3)</sup>	$V_{SD}$	$I_S = -1A, V_{GS} = 0V$			-1	V
<b>Dynamic characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		700		pF
Output capacitance	$C_{oss}$			120		pF
Reverse transfer capacitance	$C_{rss}$			75		pF
<b>Switching Characteristics</b>						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = -10V, V_{DS} = -15V,$ $R_L = 3.6\Omega, R_{GEN} = 3\Omega$		8.6		ns
Turn-on rise time	$t_r$			5.0		ns
Turn-off delay time	$t_{d(off)}$			28.2		ns
Turn-off fall time	$t_f$			13.5		ns

**Notes:**

- The power dissipation  $P_D$  is based on  $T_{J(MAX)} = 150^\circ\text{C}$ , using  $\leq 10s$   $R_{\theta JA}$ .
- The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ . The value in any given application depends on the user's specific board design.
- Pulse test: Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

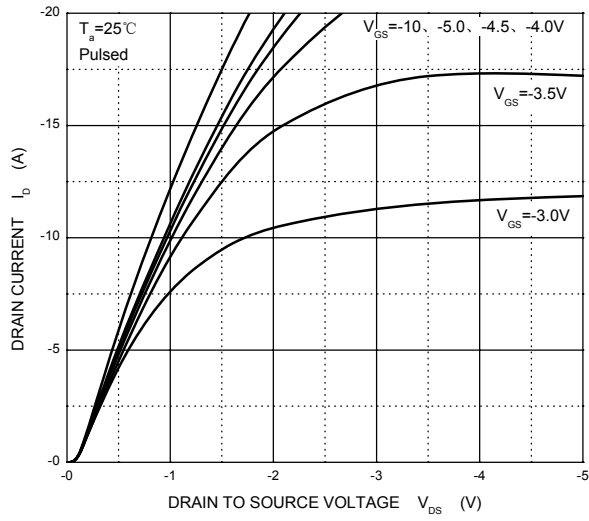


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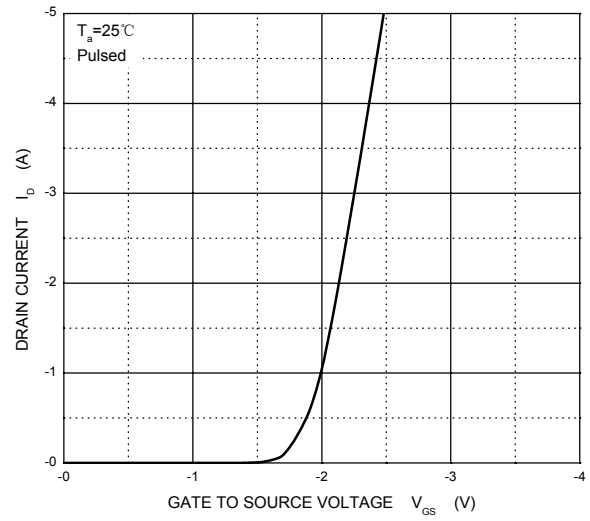
## P Enhancement Field Effect Transistor

### TYPICAL CHARACTERISTICS CURVES

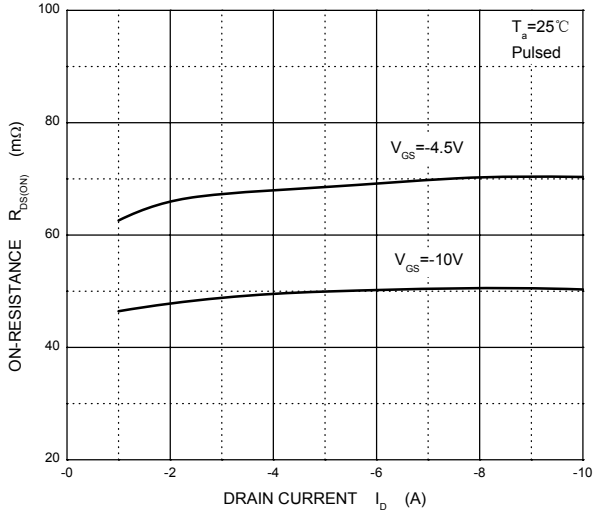
#### Output Characteristics



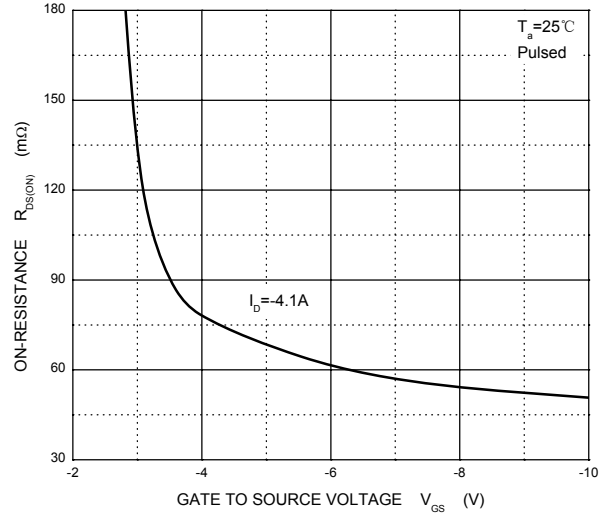
#### Transfer Characteristics



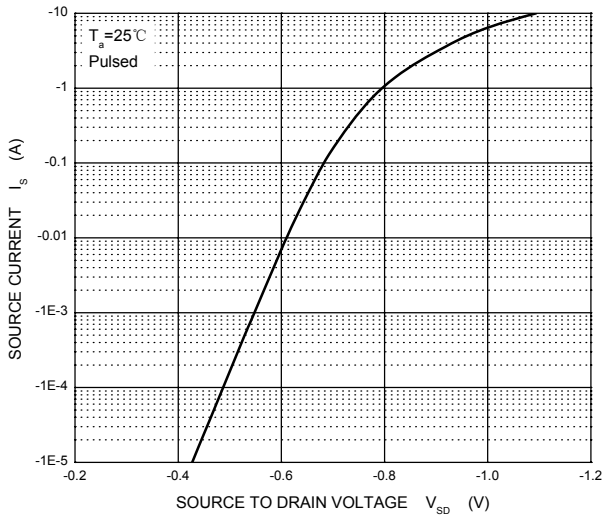
#### $R_{DS(ON)}$ — $I_D$



#### $R_{DS(ON)}$ — $V_{GS}$



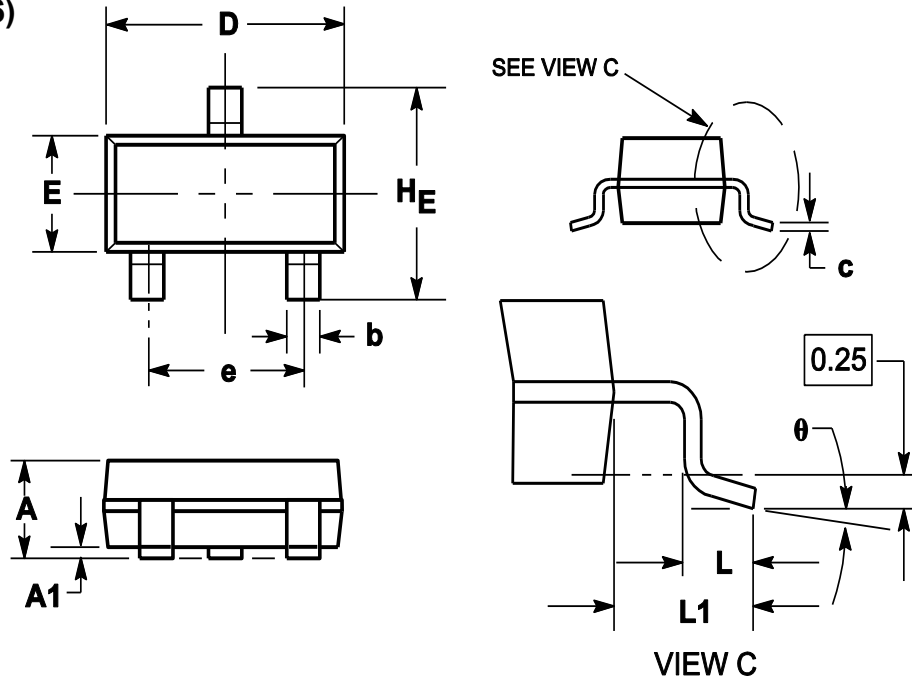
#### $I_S$ — $V_{SD}$



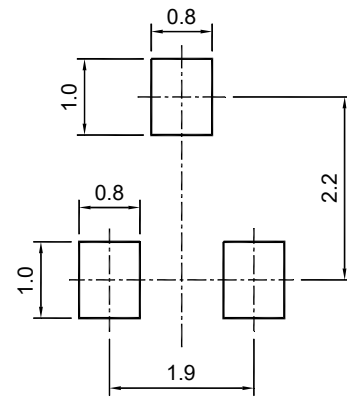


### PACKAGE OUTLINE

#### SOT-23 (TO-236)



Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.900	1.025	1.150
A1	0.000	0.050	0.100
b	0.300	0.400	0.500
c	0.080	0.115	0.150
D	2.800	2.900	3.000
E	1.200	1.300	1.400
HE	2.250	2.400	2.550
e	1.800	1.900	2.000
L1	0.550REF		
L	0.300		0.500
θ	0°		8°

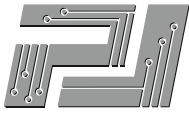


SOT-23 (TO-236)

**Recommended soldering pad**

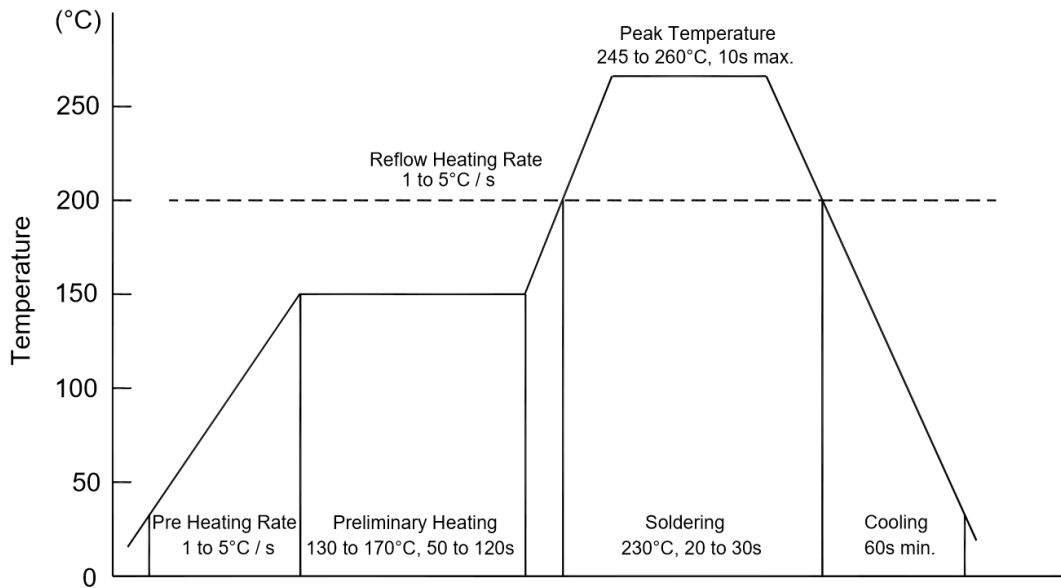
### ORDERING INFORMATION

Device	Package	Shipping
PJM3407PSA	SOT-23	3000/Reel&Tape(7inch)



### CONDITIONS OF SOLDERING AND STORAGE

#### ◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

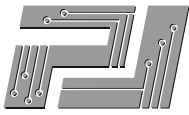
- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

#### ◆ Conditions of hand soldering

- Temperature: 370 °C
- Time: 3s max.
- Times: one time

#### ◆ Storage conditions

- **Temperature**  
5 to 40 °C
- **Humidity**  
30 to 80% RH
- **Recommended period**  
One year after manufacturing



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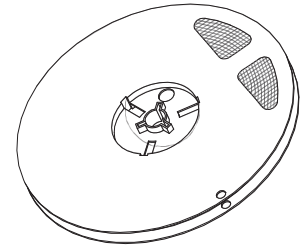
### PACKAGE SPECIFICATIONS

#### ◆ The method of packaging

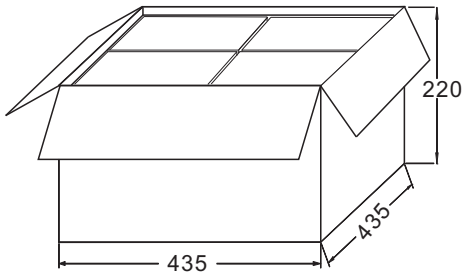
SOT-23 (TO-236)



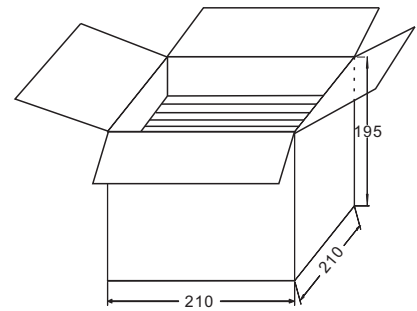
3,000 pcs per reel



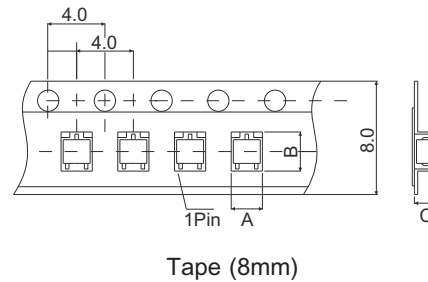
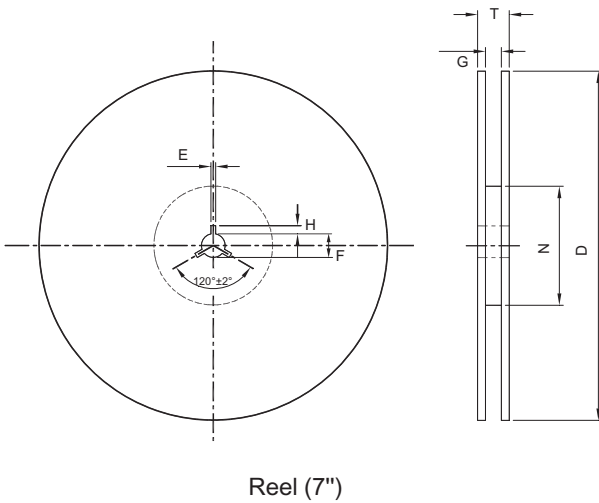
30,000 pcs per box  
10 reels per box



120,000 pcs per carton  
4 boxes per carton



#### ◆ Embossed tape and reel data



Symbol	Value (unit: mm)
A	3.15 ± 0.1
B	2.7 ± 0.1
C	1.25 ± 0.1
E	2 ± 0.5
F	13 ± 0.5
D	178 ± 2.0
G	8.4 ± 1.5
H	4 ± 0.5
N	60
T	< 14.9